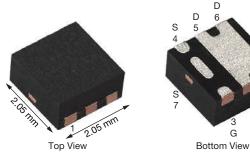


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Vishay Siliconix

# Automotive P-Channel 20 V (D-S) 175 °C MOSFET

# PowerPAK® SC-70-6L Single



Marking Code: QBXXXX

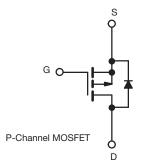
PRODUCT SUMMARY								
V <sub>DS</sub> (V)	-20							
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.125							
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -2.5 \text{ V}$	0.205							
I <sub>D</sub> (A)	-3.75							
Configuration	Single							
Package	PowerPAK SC-70							

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912







PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	-20	V	
Gate-source voltage		$V_{GS}$	± 12	V	
Continuous drain current	T <sub>C</sub> = 25 °C		-3.75		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-3.75	A	
Continuous source current (diode conduct	tion) <sup>a</sup>	I <sub>S</sub>	3.75		
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-12		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-8		
Single pulse avalanche energy	L = U. I MIH	E <sub>AS</sub>	3.2	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Б	13.6	w	
waxiinum power dissipation -	T <sub>C</sub> = 125 °C	$P_{D}$	4.5		
Operating junction and storage temperatu	T <sub>J</sub> , T <sub>stq</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	LIMIT	UNIT					
Junction-to-ambient	PCB mount c	R <sub>thJA</sub>	90	°C/W					
Junction-to-case (drain)		$R_{thJF}$	11	C/VV					

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static	OTWIDOL	120	T CONDITIONS		1	WAX.	Oitii	
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = -250 \mu\text{A}$		-20	Ι _	<u> </u>		
Gate-source threshold voltage	V <sub>GS(th)</sub>	uc-	$V_{GS}$ , $I_D = -250 \mu A$	-0.6	-1.0	-1.5	V	
Gate-source leakage	I <sub>GSS</sub>	20	$0 \text{ V, V}_{GS} = \pm 12 \text{ V}$	-	-	± 100	nA	
date source leakage	1G55	$V_{DS} = 0 \text{ V}, V_{GS} = 112 \text{ V}$ $V_{GS} = 0 \text{ V}$ $V_{DS} = -20 \text{ V}$			_	-1	шл	
Zero gate voltage drain current	lana	4.4	$V_{DS} = -20 \text{ V}$ $V_{DS} = -20 \text{ V}, T_{J} = 125 \text{ °C}$		_	-50	μΑ	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V}$ $V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}, T_J = 125 \text{ °C}$ $V_{DS} = -20 \text{ V}, T_J = 175 \text{ °C}$			-150		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = 20 \text{ V}, 15 = 173 \text{ O}$ $V_{DS} \ge 5 \text{ V}$	-8	_	-130	Α	
On-state drain current	'D(on)	$V_{GS} = -4.5 \text{ V}$		-0	0.085	0.125		
			I <sub>D</sub> = -2.4 A, T <sub>J</sub> = 125 °C		-	0.125		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	0.0	$I_D = -2.4 \text{ A}, T_J = 175 \text{ °C}$		_	0.200	Ω	
		$V_{GS} = -2.5 \text{ V}$			0.160	0.205	1	
Forward transconductance b		$V_{GS} = -2.3 \text{ V}$ $I_D = -1.6 \text{ A}$ $I_D = -2.4 \text{ A}$			6	-	S	
Dynamic b	915	- 55	10 1,10 21171					
Input capacitance	C <sub>iss</sub>			_	265	330	1	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}$ $V_{DS} = -10 \text{ V}, f = 1 \text{ MHz}$		-	75	94	pF	
Reverse transfer capacitance	C <sub>rss</sub>	- 143	103 111,1 1111	_	50	63	- F	
Total gate charge c	Q <sub>q</sub>			-	3.4	5.5		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A}$	-	0.6	-	nC	
Gate-drain charge c	Q <sub>qd</sub>		103 111,10 =1111	-	1.1	-	1	
Gate resistance	R <sub>g</sub>	f = 1 MHz		4.8	9.6	14.4	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>				20	30	ns	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	-	18	27			
Turn-off delay time c	t <sub>d(off)</sub>	$I_D \cong -1.9 \text{ A},$	-	19	28			
Fall time <sup>c</sup>	t <sub>f</sub>	7	-	-	8	12		
Source-Drain Diode Ratings and Char					<u> </u>	<u> </u>		
Pulsed current <sup>a</sup>		_	_	-12.7	Α			
Forward voltage	I <sub>SM</sub> V <sub>SD</sub>	l <sub>E</sub> :		-0.8	-1.2	V		

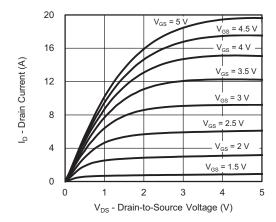
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

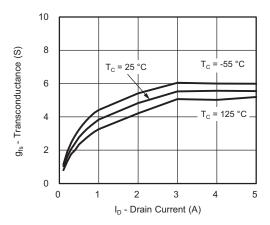
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



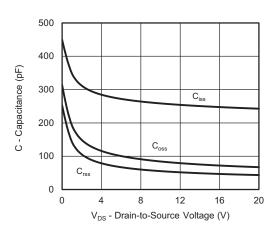
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



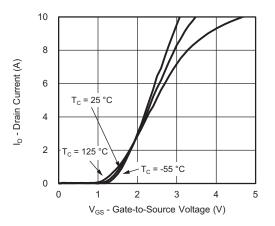
#### **Output Characteristics**



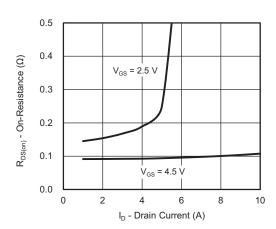
### Transconductance



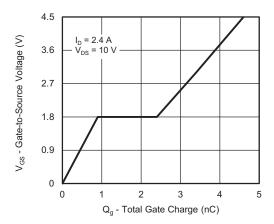
Capacitance



#### **Transfer Characteristics**



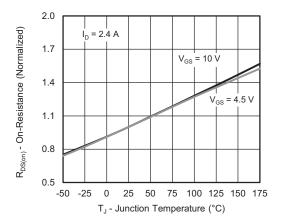
On-Resistance vs. Drain Current



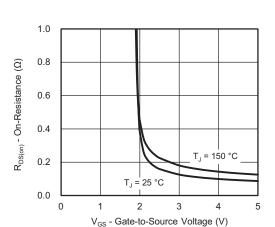
**Gate Charge** 



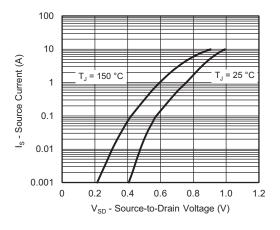
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



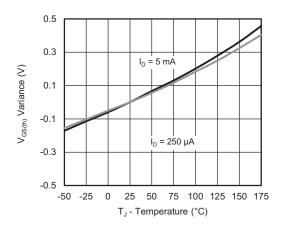
On-Resistance vs. Junction Temperature



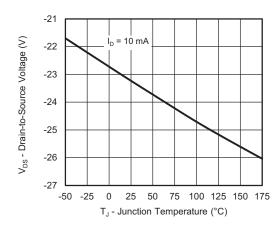
On-Resistance vs. Gate-to-Source Voltage



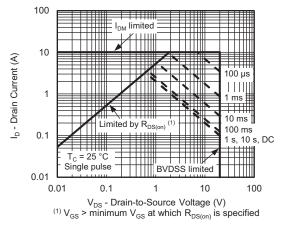
Source-Drain Diode Forward Voltage



**Threshold Voltage** 



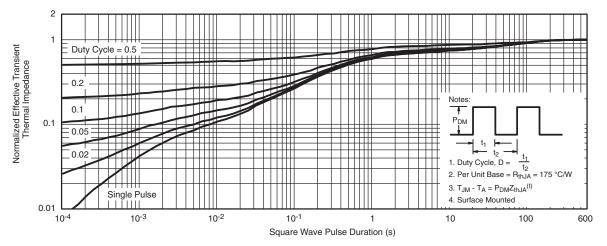
**Drain Source Breakdown vs. Junction Temperature** 



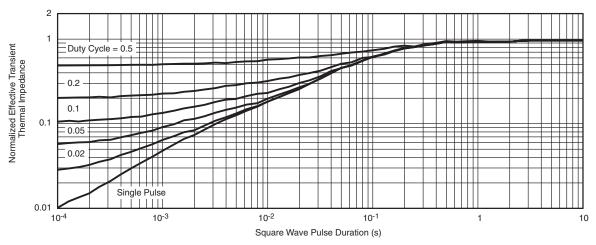
Safe Operating Area



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

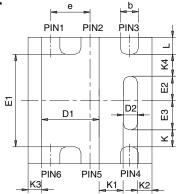
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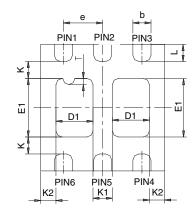




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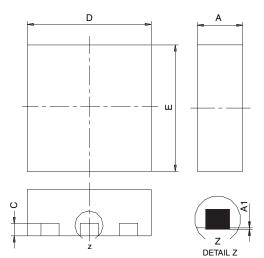
### PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
   Package outline exclusive of mold flash and metal burr
   Package outline inclusive of plating

			SINGL	_E PAD			DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC			
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	1		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1	0.009 TYP			0.252 TYP			0.010 TYP			
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	1	0.014 TYP									
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
ECNI- C C	7404 D	. 0 00 1	. 07										

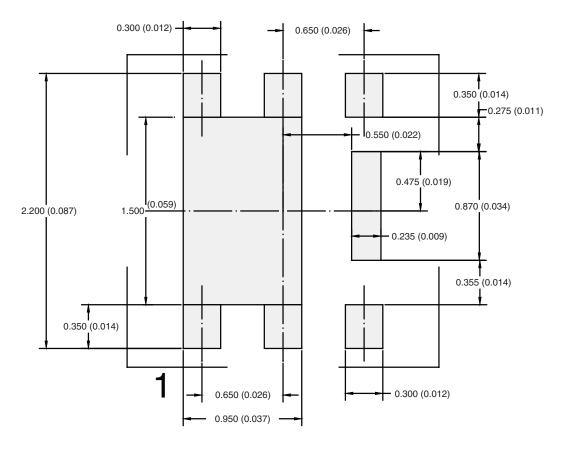
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



### RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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